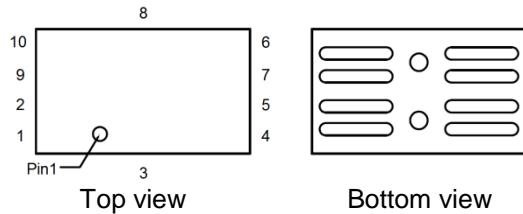
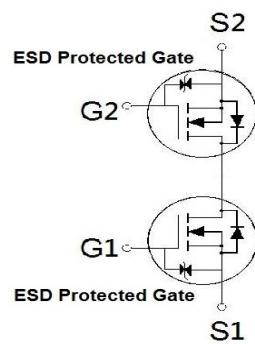


NIKO-SEM**Common Drain N-Channel
Power MOSFET****PQ6X6JN
WLCSP****Halogen-Free & Lead-Free****PRODUCT SUMMARY**

$V_{(BR)SSS}$	$R_{SS(ON)}$	I_S
12V	2.75mΩ	19A



1,2,4,5. Source1
3. Gate1
6,7,9,10. Source2
8. Gate2

**ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS	SYMBOL	LIMITS	UNITS
Source-Source Voltage	V_{SSS}	12	V
Gate-Source Voltage	V_{GSS}	± 8	V
Continuous Source Current	I_S	19	A
Pulsed Source Current ¹	I_{SP}	100	
Total Dissipation ²	P_T	1.8	W
Thermal Resistance ²	R_{QJA}	67	°C / W
Operating Junction & Storage Temperature Range	T_j, T_{stg}	-55 to 150	°C

¹ $PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$.²When mounted on 1in² FR-4 board.**ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$, Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Source-Source Breakdown Voltage	$V_{(BR)SSS}$	$V_{GS} = 0\text{V}, I_S = 1\text{mA}$	12			V
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{SS} = V_{GS}, I_S = 1\text{mA}$		0.9	1.4	
Gate-Source Leakage	I_{GSS}	$V_{SS} = 0\text{V}, V_{GS} = \pm 8\text{V}$			± 10	μA
		$V_{SS} = 0\text{V}, V_{GS} = \pm 5\text{V}$			± 1	
Zero Gate Voltage Source Current	I_{SSS}	$V_{SS} = 12\text{V}, V_{GS} = 0\text{V}$			1	μA
Source-Source On-State Resistance ¹	$R_{SS(ON)}$	$V_{GS} = 4.5\text{V}, I_S = 6\text{A}$		2.1	2.75	$\text{m}\Omega$
		$V_{GS} = 3.8\text{V}, I_S = 6\text{A}$		2.2	2.85	
		$V_{GS} = 3.1\text{V}, I_S = 6\text{A}$		2.4	3.95	
		$V_{GS} = 2.5\text{V}, I_S = 6\text{A}$		3.1	6.1	

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DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 10V, f = 100KHz$		2639		pF
Output Capacitance	C_{oss}			638		
Reverse Transfer Capacitance	C_{rss}			545		
Total Gate Charge ²	Q_g	$V_{SS} = 6V, V_{GS} = 4V$ $I_S = 6A$		32		nC
Turn-On Delay Time ²	$t_{d(on)}$			1.8		
Rise Time ²	t_r			3.2		
Turn-Off Delay Time ²	$t_{d(off)}$			4.6		
Fall Time ²	t_f			5.5		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ C$)						
Forward Source-Source Voltage ¹	V_F	$I_S = 6A, V_{GS} = 0V$		0.6		V

¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.²Independent of operating temperature.